MC74LVX50

Hex Buffer

The MC74LVX50 is an advanced high speed CMOS buffer fabricated with silicon gate CMOS technology.

The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: t_{PD} = 4.1 ns (Typ) at V_{CC} = 3.3 V
- Low Power Dissipation: I_{CC} = 2 μA (Max) at T_A = 25°C
- High Noise Immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC}
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 3.6 V Operating Range
- Low Noise: V_{OLP} = 0.5 V (Max)
- These Devices are Pb−Free and are RoHS Compliant

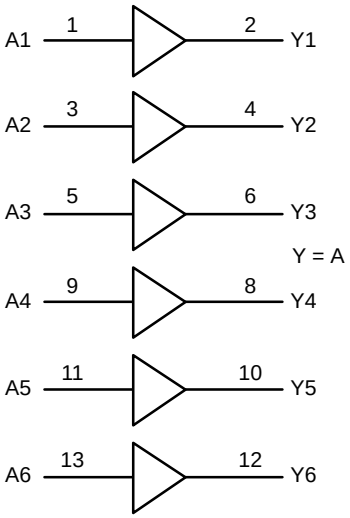

Figure 1. Logic Diagram

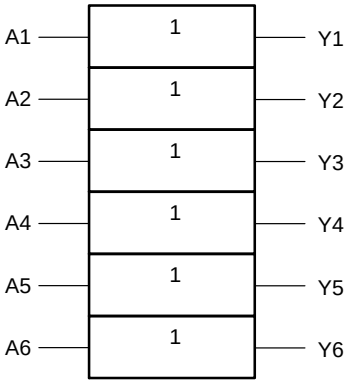

Figure 2. Logic Symbol

FUNCTION TABLE

A Input	Y Output
L	L
H	H

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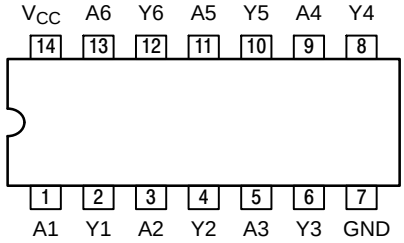
SOIC−14 NB
D SUFFIX
CASE 751A

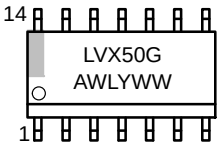
TSSOP−14
DT SUFFIX
CASE 948G

PIN ASSIGNMENT

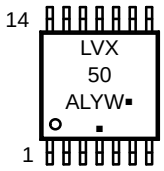


14−Lead (Top View)

MARKING DIAGRAMS



SOIC−14 NB



TSSOP−14

LVX50 = Specific Device Code
A = Assembly Location
WL, L = Wafer Lot
Y = Year
WW, W = Work Week
G or ▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	DC Input Voltage		−0.5 to +7.0	V
V_{OUT}	DC Output Voltage		−0.5 to V_{CC} +0.5	V
I_{IK}	DC Input Diode Current	V_I < GND	−20	mA
I_{OK}	DC Output Diode Current	V_O < GND	±20	mA
I_{OUT}	DC Output Sink Current		±25	mA
I_{CC}	DC Supply Current per Supply Pin		±50	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	(Note 1) SOIC TSSOP	 125 170	°C/W
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 30% − 35%	UL 94−V0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 2000	V
$I_{Latchup}$	Latchup Performance	Above V_{CC} and Below GND at 85°C (Note 5)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2−ounce copper trace with no air flow.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to JESD22−C101−A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Supply Voltage		2.0	3.6	V
V_I	Input Voltage	(Note 6)	0	5.5	V
V_O	Output Voltage	(HIGH or LOW State)	0	V_{CC}	V
T_A	Operating Free−Air Temperature		−40	+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate	V_{CC} = 3.0 V ±0.3 V	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

6. Unused inputs may not be left open. All inputs must be tied to a high− or low−logic input voltage level.

NOTE: The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			$T_A \le 85°C$		Unit
				Min	Typ	Max	Min	Max	
V_{IH}	High−Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V_{IL}	Low−Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V_{OH}	High−Level Output Voltage (V_{IN}= V_{IH} or V_{IL})	I_{OH} = −50 μA I_{OH} = −50 μA I_{OH} = −4 mA	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V_{OL}	Low−Level Output Voltage (V_{IN}= V_{IH} or V_{IL})	I_{OL} = 50 μA I_{OL} = 50 μA I_{OL} = 4 mA	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
I_{IN}	Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 3.6			±0.1		±1.0	μA
I_{CC}	Quiescent Supply Current	V_{IN} = V_{CC} or GND	3.6			2.0		20.0	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS Input t_r = t_f = 3.0 ns

Symbol	Parameter	Test Conditions		T_A = 25°C			$T_A \le 85°C$		Unit
				Min	Typ	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, Input A to Y	V_{CC} = 2.7 V	C_L = 15 pF C_L = 50 pF		5.4 7.9	10.1 13.6	1.0 1.0	12.5 16.0	ns
		V_{CC} = 3.3 V ± 0.3 V	C_L = 15 pF C_L = 50 pF		4.1 6.6	6.2 9.7	1.0 1.0	7.5 11.5	
t_{OSHL} t_{OSLH}	Output−to−Output Skew (Note 7)	V_{CC} = 2.7 V	C_L = 50 pF			1.5		1.5	ns
		V_{CC} = 3.3 V ±0.3V	C_L = 50 pF			1.5		1.5	
C_{IN}	Input Capacitance				4	10		10	pF
				Typical @ 25°C, V_{CC} = 3.3 V					
C_{PD}	Power Dissipation Capacitance (Note 8)				15				pF

7. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH−to−LOW (t_{OSHL}) or LOW−to−HIGH (t_{OSLH}); parameter guaranteed by design.
8. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

NOISE CHARACTERISTICS Input t_r = t_f = 3.0ns, C_L = 50pF, V_{CC} = 3.3 V

Symbol	Characteristic	T_A = 25°C		Unit
		Typ	Max	
V_{OLP}	Quiet Output Maximum Dynamic V_{OL}	0.3	0.5	V
V_{OLV}	Quiet Output Minimum Dynamic V_{OL}	−0.3	−0.5	V
V_{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V

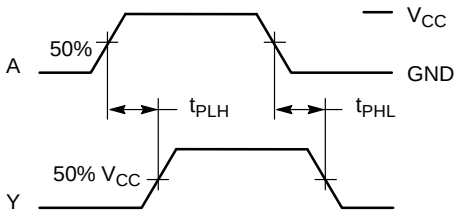
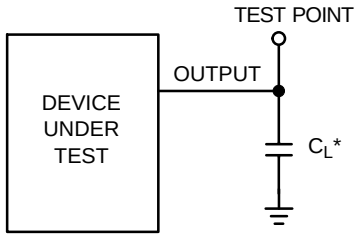


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

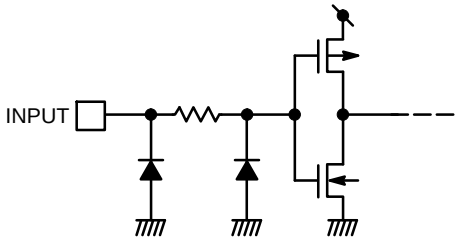
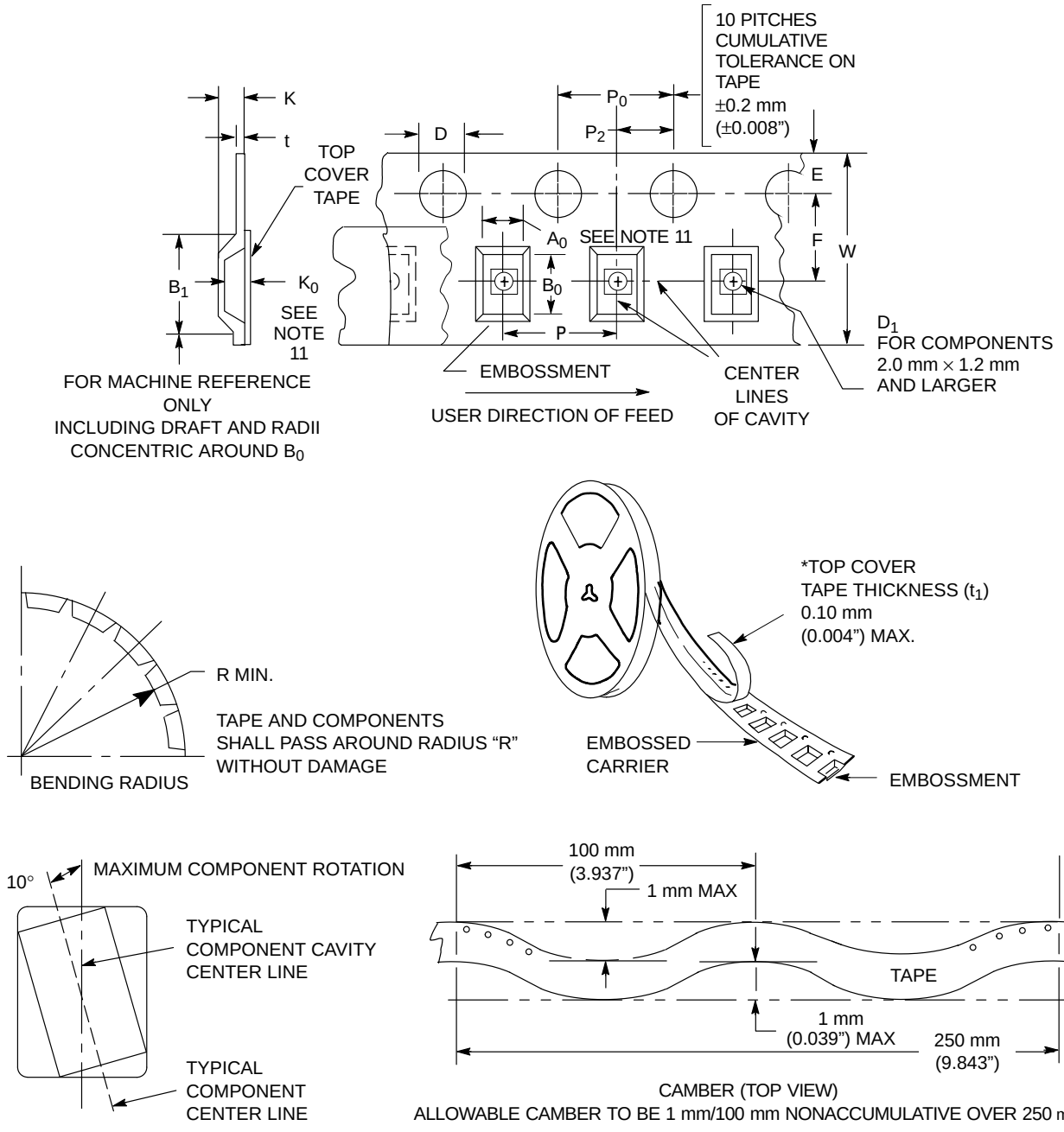


Figure 5. Input Equivalent Circuit

EMBOSSED CARRIER DIMENSIONS (See Notes 9 and 10)

Tape Size	B_1 Max	D	D_1	E	F	K	P	P_0	P_2	R	T	W
8 mm	4.35 mm (0.179”)	1.5 mm + 0.1 −0.0 (0.059” +0.004 −0.0)	1.0 mm Min (0.179”)	1.75 mm ±0.1 (0.069 ±0.004”)	3.5 mm ±0.5 (1.38 ±0.002”)	2.4 mm Max (0.094”)	4.0 mm ±0.10 (0.157 ±0.004”)	4.0 mm ±0.1 (0.157 ±0.004”)	2.0 mm ±0.1 (0.079 ±0.004”)	25 mm (0.98”)	0.6 mm (0.024)	8.3 mm (0.327)
12 mm	8.2 mm (0.323”)		1.5 mm Min (0.060)		5.5 mm ±0.5 (0.217 ±0.002”)	6.4 mm Max (0.252”)	4.0 mm ±0.10 (0.157 ±0.004”) 8.0 mm ±0.10 (0.315 ±0.004”)			30 mm (1.18”)		12.0 mm ±0.3 (0.470 ±0.012”)
16 mm	12.1 mm (0.476”)				7.5 mm ±0.10 (0.295 ±0.004”)	7.9 mm Max (0.311”)	4.0 mm ±0.10 (0.157 ±0.004”) 8.0 mm ±0.10 (0.315 ±0.004”) 12.0 mm ±0.10 (0.472 ±0.004”)					16.3 mm (0.642)
24 mm	20.1 mm (0.791”)				11.5 mm ±0.10 (0.453 ±0.004”)	11.9 mm Max (0.468”)	16.0 mm ±0.10 (0.63 ±0.004”)					24.3 mm (0.957)

9. Metric Dimensions Govern−English are in parentheses for reference only.
10. A_0, B_0, and K_0 are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity



11. A_0, B_0, and K_0 are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

Figure 6. Carrier Tape Specifications

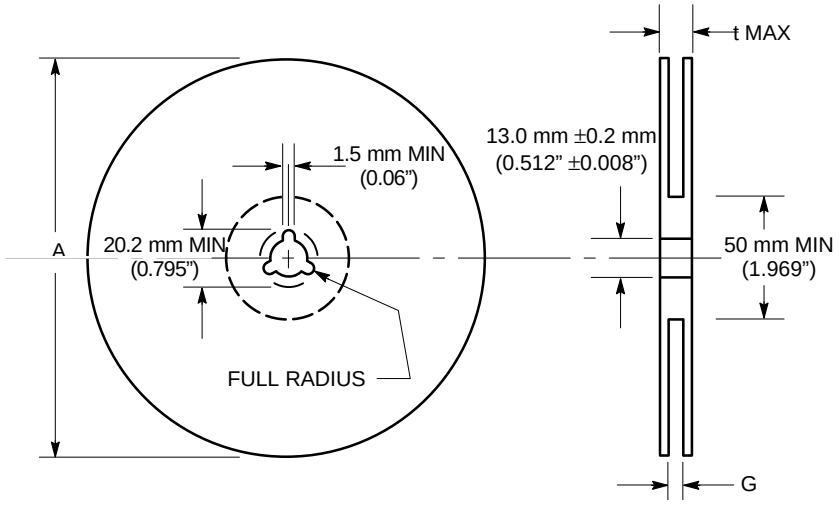


Figure 7. Reel Dimensions

REEL DIMENSIONS

Tape Size	T&R Suffix	A Max	G	t Max
8 mm	T1, T2	178 mm (7”)	8.4 mm, +1.5 mm, −0.0 (0.33” + 0.059”, −0.00)	14.4 mm (0.56”)
8 mm	T3, T4	330 mm (13”)	8.4 mm, +1.5 mm, −0.0 (0.33” + 0.059”, −0.00)	14.4 mm (0.56”)
12 mm	R2	330 mm (13”)	12.4 mm, +2.0 mm, −0.0 (0.49” + 0.079”, −0.00)	18.4 mm (0.72”)
16 mm	R2	360 mm (14.173”)	16.4 mm, +2.0 mm, −0.0 (0.646” + 0.078”, −0.00)	22.4 mm (0.882”)
24 mm	R2	360 mm (14.173”)	24.4 mm, +2.0 mm, −0.0 (0.961” + 0.078”, −0.00)	30.4 mm (1.197”)

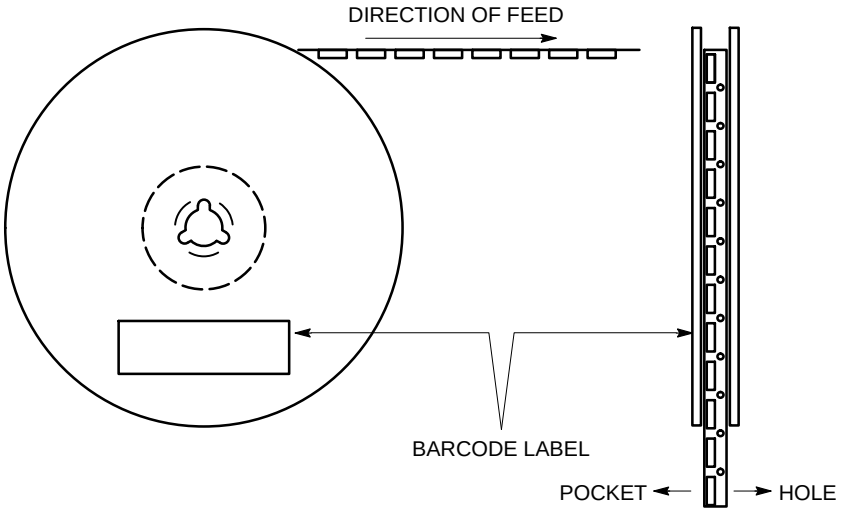


Figure 8. Reel Winding Direction

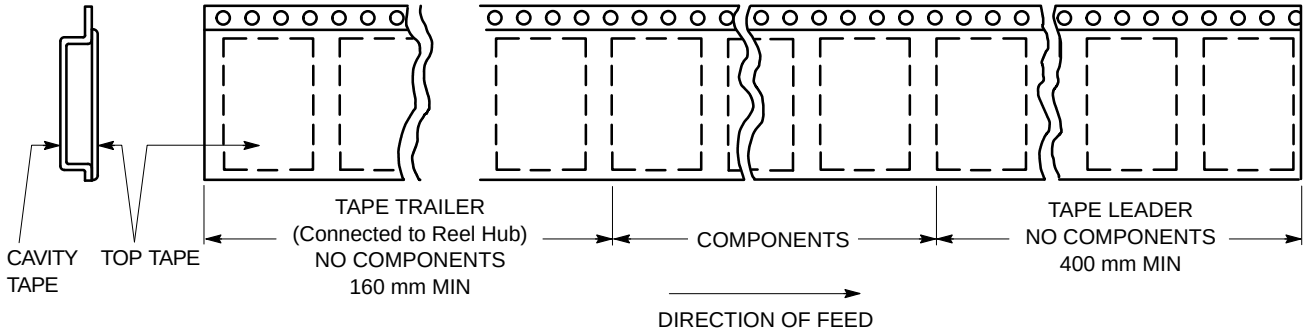


Figure 9. Tape Ends for Finished Goods

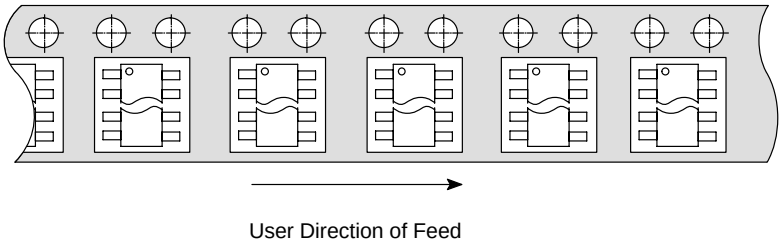


Figure 10. TSSOP and SOIC R2 Reel Configuration/Orientation

TAPE UTILIZATION BY PACKAGE

Tape Size	SOIC	TSSOP	QFN	SC88A / SOT−353 SC88/SOT−363
8 mm				5−, 6−Lead
12 mm	8−Lead	8−, 14−, 16−Lead	8−, 14−, 16−Lead	
16 mm	14−, 16−Lead	20−, 24−Lead	20−, 24−Lead	
24 mm	18−, 20−, 24−, 28−Lead	48−, 56−Lead	48−, 56−Lead	

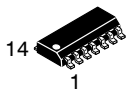
ORDERING INFORMATION

Device	Package	Shipping†
MC74LVX50DG	SOIC−14 NB (Pb−Free)	55 Units / Rail
MC74LVX50DR2G	SOIC−14 NB (Pb−Free)	2500 Tape & Reel
MC74LVX50DTG	TSSOP−14 (Pb−Free)	96 Units / Rail
MC74LVX50DTR2G	TSSOP−14 (Pb−Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

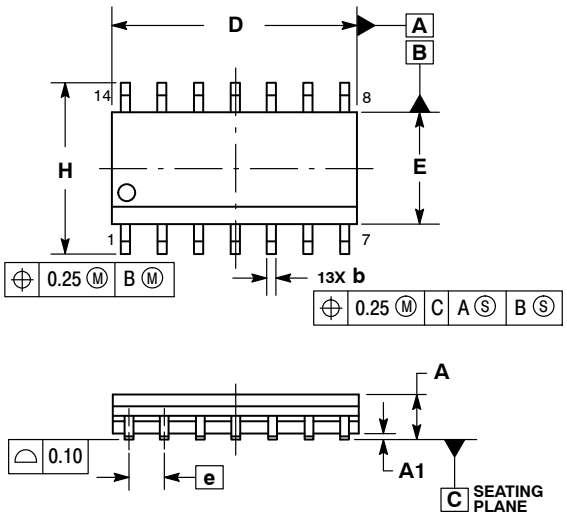
ON Semiconductor®

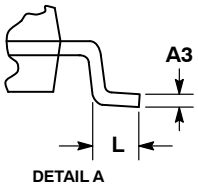


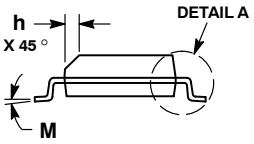
SCALE 1:1

SOIC−14 NB
CASE 751A−03
ISSUE L

DATE 03 FEB 2016



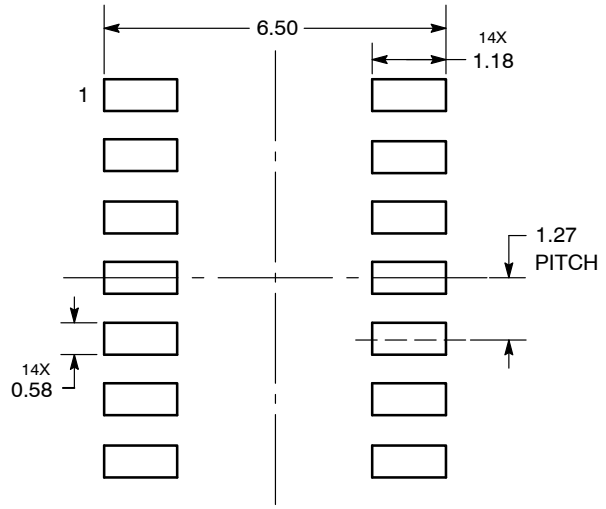




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

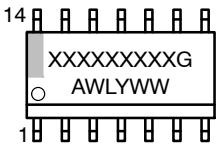
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	SOIC−14 NB		PAGE 1 OF 2

SOIC−14
CASE 751A−03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

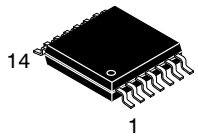
STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

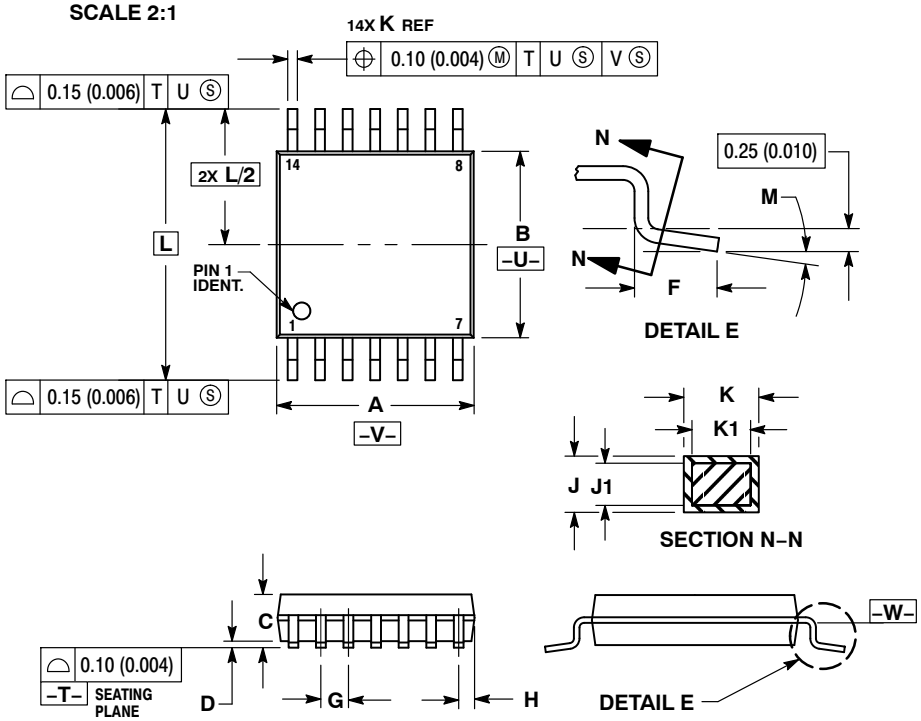
ON Semiconductor®

TSSOP−14 WB
CASE 948G
ISSUE C

DATE 17 FEB 2016



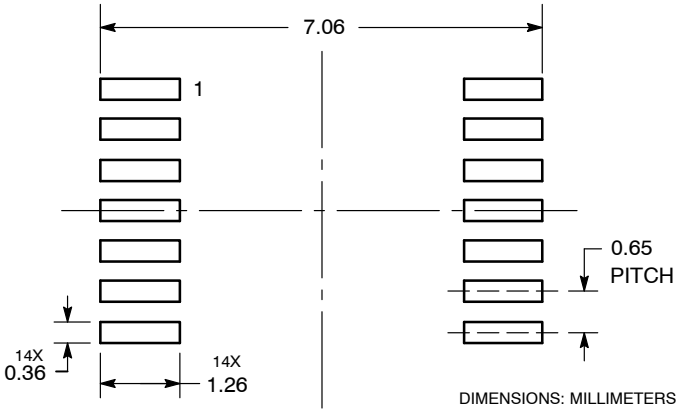
SCALE 2:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

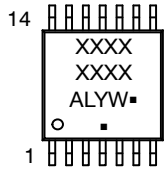
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

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DESCRIPTION:	**TSSOP−14 WB**	**PAGE 1 OF 1**

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